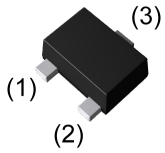
SL002N02K

Nch 20V 200mA Small Signall MOSFET

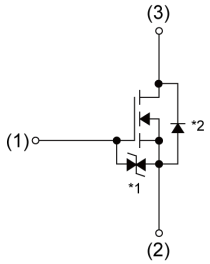
V_{DSS}	20V
$R_{DS(on)}$(Max.)	1.2Ω
I_D	±200mA
P_D	150mW

●Outline

SOT-723



●Inner circuit



(1) Gate
(2) Source
(3) Drain

*1 ESD Protection Diode
*2 Body Diode

●Features

1) Small Package (SOT723).
2) Ultra Low voltage drive (1.2V drive).
3) Pb-free lead plating ; RoHS compliant.
4) Halogen Free.

●Application

Switching

●Absolute maximum ratings (T_a = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	20	V
Continuous drain current	I_D	±200	mA
Pulsed drain current	I_{DP} *1	±400	mA
Gate - Source voltage	V_{GSS}	±8	V
Power dissipation	P_D *2	150	mW
Junction temperature	T_j	150	℃
Operating junction and storage temperature range	T_{stg}	-55 to +150	℃

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	R_{thJA} *2	-	-	833	℃/W

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	20	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	I_D = 1mA referenced to 25℃	-	29.0	-	mV/℃
Zero gate voltage drain current	I_{DSS}	V_{DS} = 20V, V_{GS} = 0V	-	-	1	μA
Gate - Source leakage current	I_{GSS}	V_{GS} = ±8V, V_{DS} = 0V	-	-	±10	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = 10V, I_D = 1mA	0.3	-	1.0	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	I_D = 1mA referenced to 25℃	-	-1.6	-	mV/℃
Static drain - source on - state resistance	$R_{DS(on)}$ *3	V_{GS} = 2.5V, I_D = 200mA	-	0.8	1.2	Ω
		V_{GS} = 1.8V, I_D = 200mA	-	1.0	1.4	
		V_{GS} = 1.5V, I_D = 40mA	-	1.2	2.4	
		V_{GS} = 1.2V, I_D = 20mA	-	1.6	4.8	
Forward Transfer Admittance	$\|Y_{fs}\|$ *3	V_{DS} = 10V, I_D = 200mA	200	-	-	mS

*1 Pw≦10μs , Duty cycle≦1%

*2 Each terminal mounted on a reference land.

*3 Pulsed

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	V_{GS} = 0V	-	25	-	pF
Output capacitance	C_{oss}	V_{DS} = 10V	-	10	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	10	-	
Turn - on delay time	$t_{d(on)}$ *3	V_{DD} ≃ 10V,V_{GS} = 4.0V	-	5	-	ns
Rise time	t_r *3	I_D = 150mA	-	10	-	
Turn - off delay time	$t_{d(off)}$ *3	R_L ≃ 67Ω	-	15	-	
Fall time	t_f *3	R_G = 10Ω	-	10	-	

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous forward current	I_S	T_a = 25℃	-	-	100	mA
Pulse forward current	I_{SP} *1		-	-	400	mA
Forward voltage	V_{SD} *3	V_{GS} = 0V, I_S = 100mA	-	-	1.2	V

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

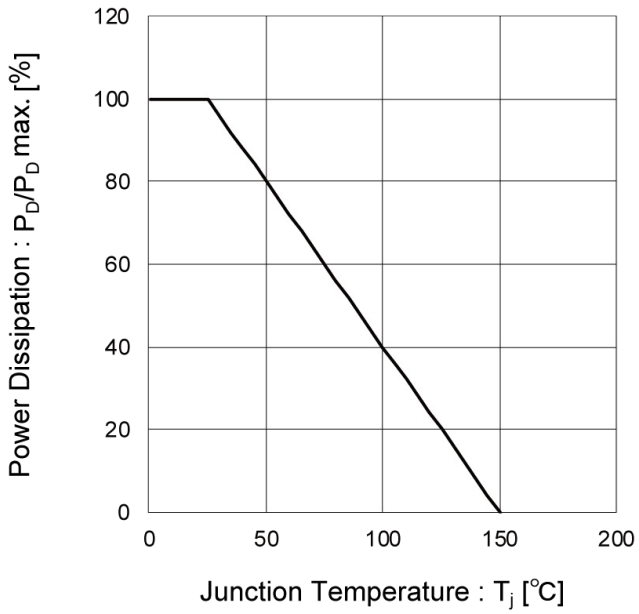


Fig.2 Drain Current Derating Curve

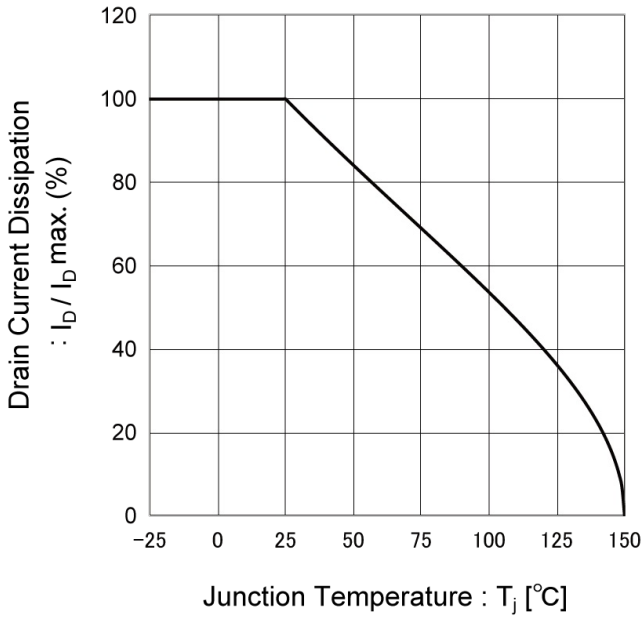


Fig.3 Typical Output Characteristics(I)

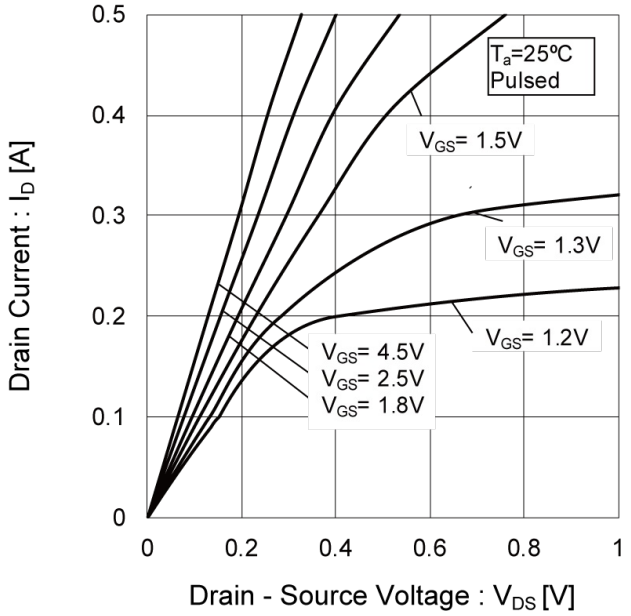
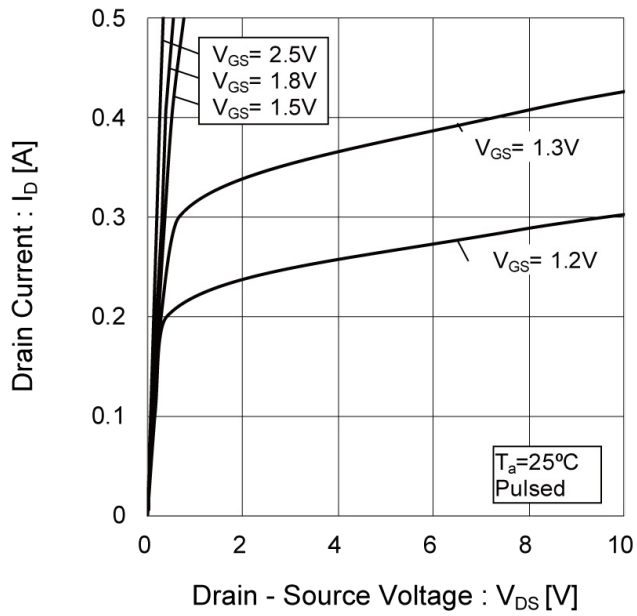


Fig.4 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.5 Breakdown Voltage vs. Junction Temperature

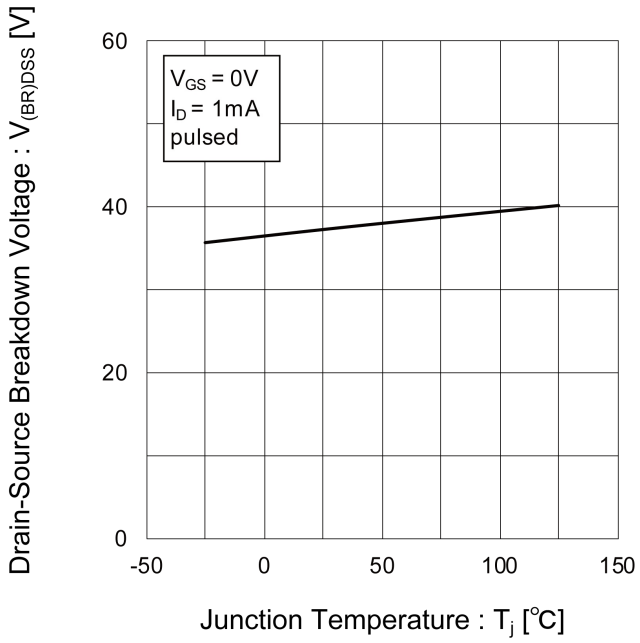


Fig.6 Typical Transfer Characteristics

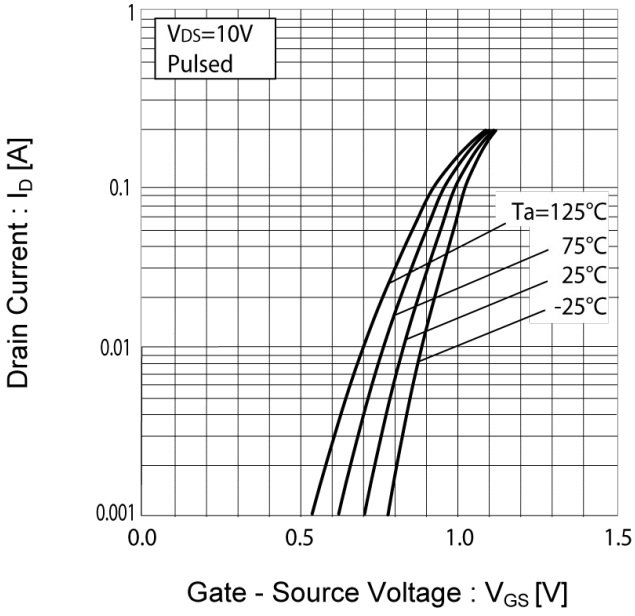


Fig.7 Gate Threshold Voltage vs. Junction Temperature

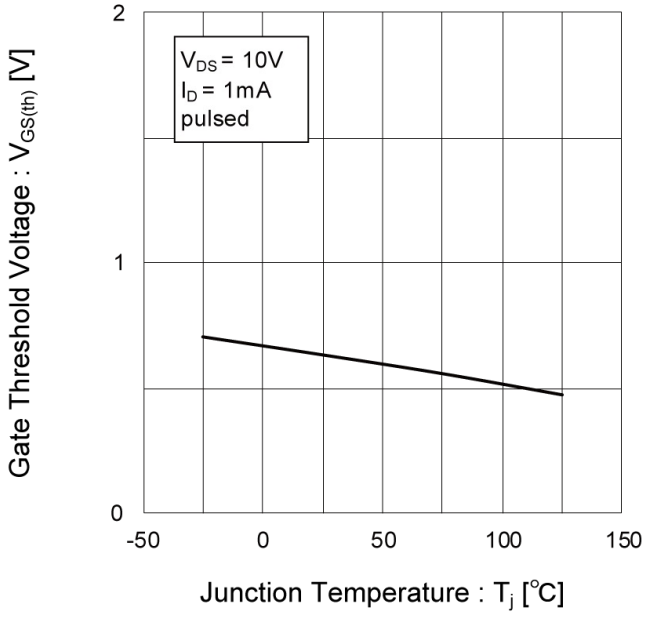
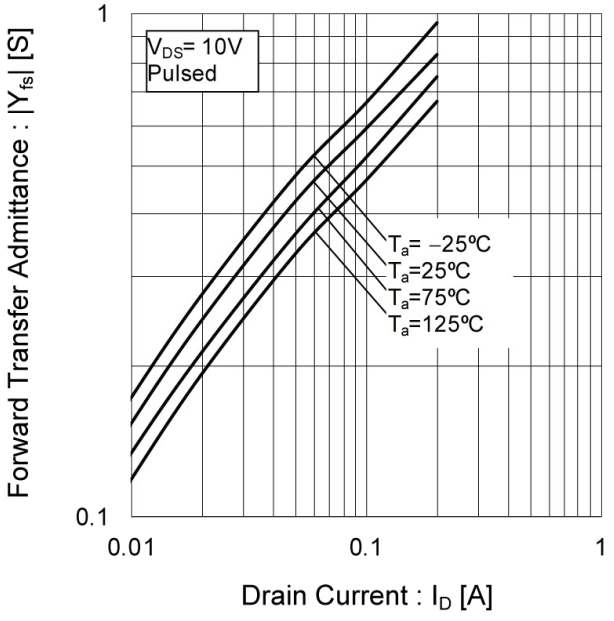


Fig.8 Forward Transfer Admittance vs. Drain Current



●Electrical characteristic curves

Fig.9 Static Drain - Source On - State Resistance vs. Gate Source Voltage

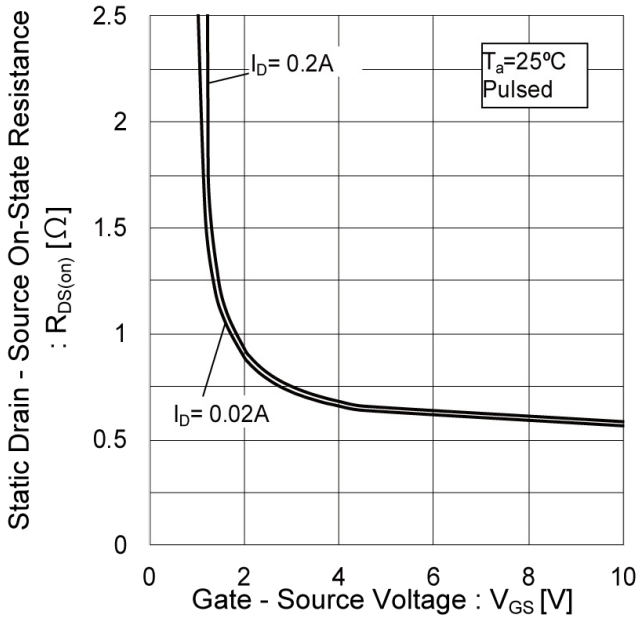


Fig.10 Static Drain - Source On - State Resistance vs. Junction Temperature

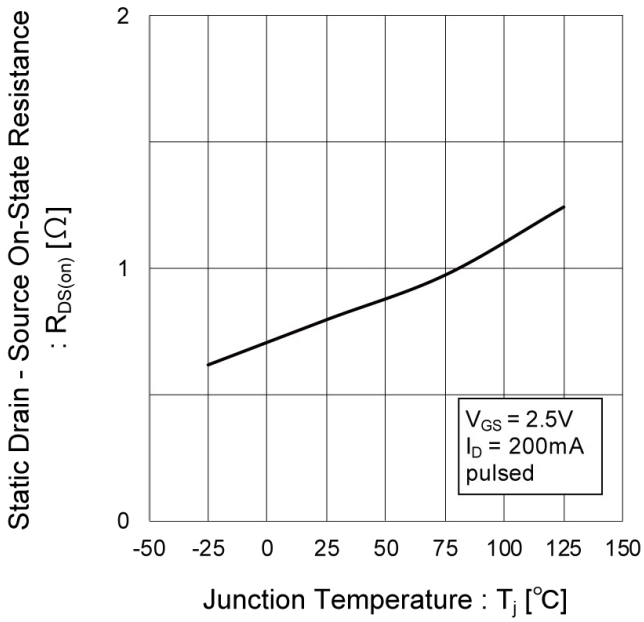
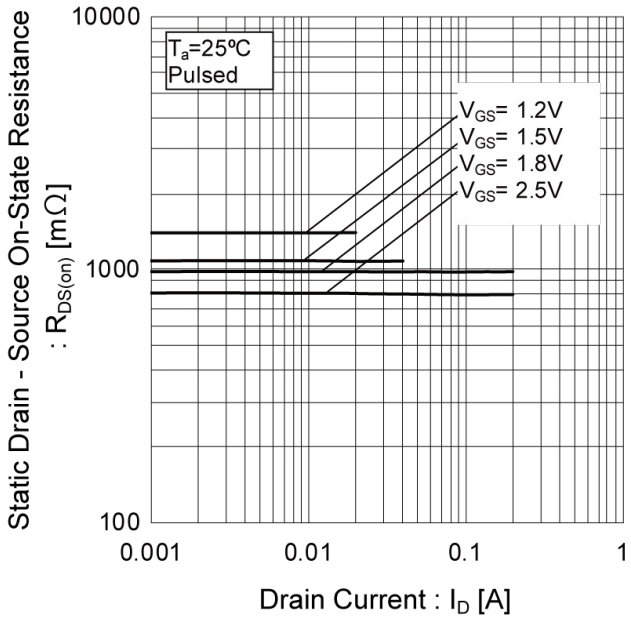


Fig.11 Static Drain - Source On - State Resistance vs. Drain Current (I)



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Drain Current (II)

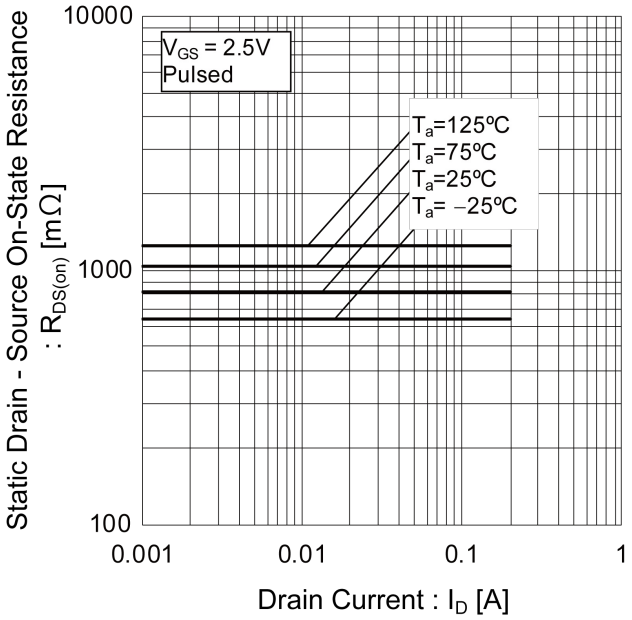


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current (III)

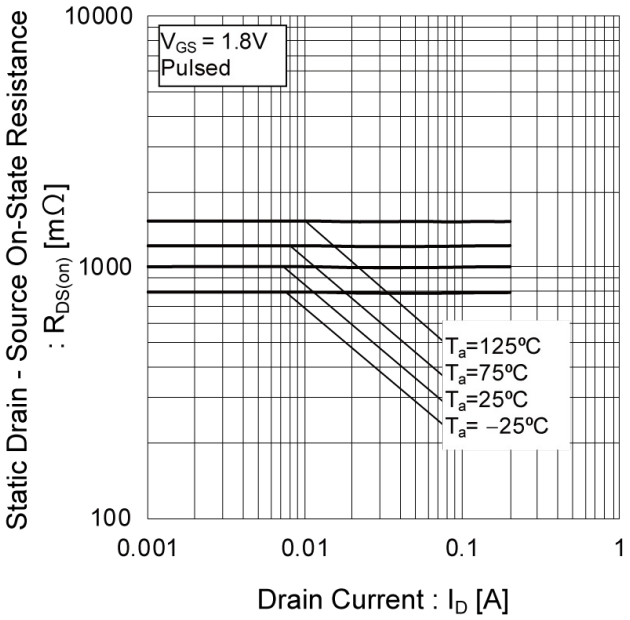


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (IV)

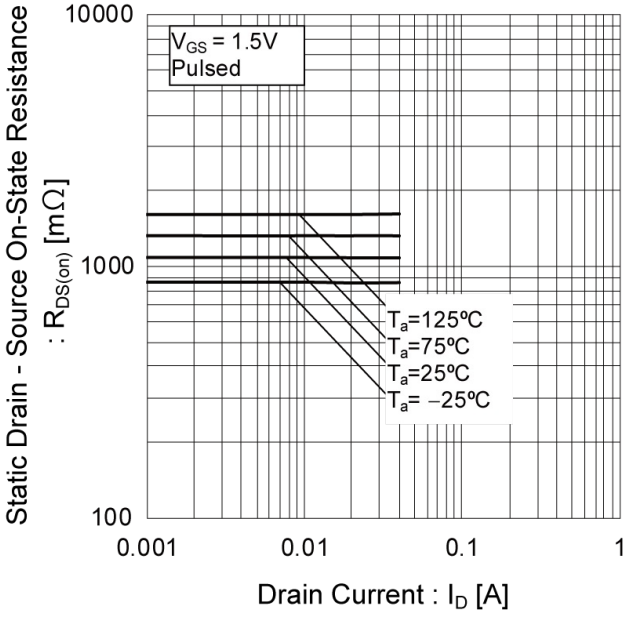
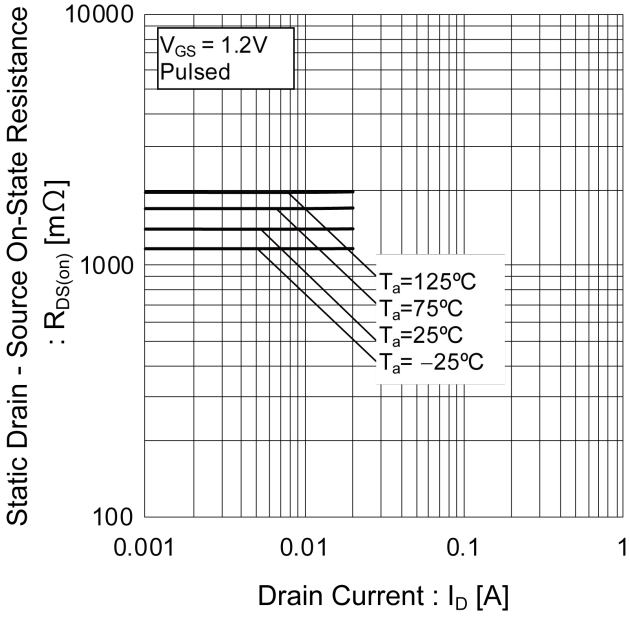


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current (V)



●Electrical characteristic curves

Fig.16 Typical Capacitance vs. Drain - Source Voltage

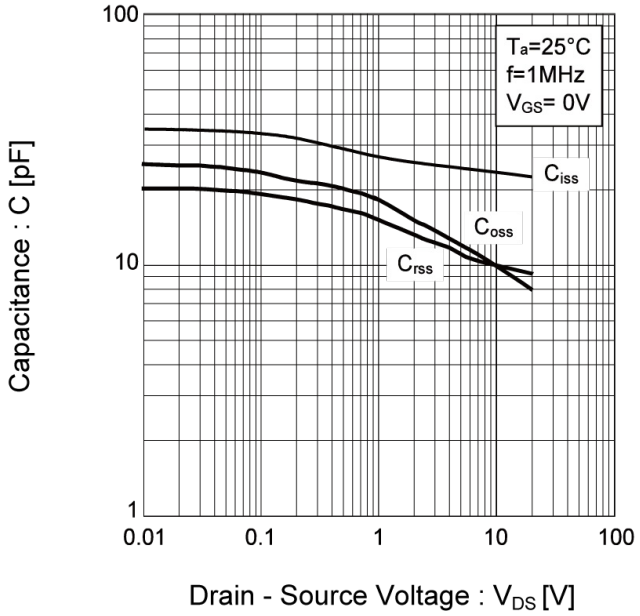


Fig.17 Switching Characteristics

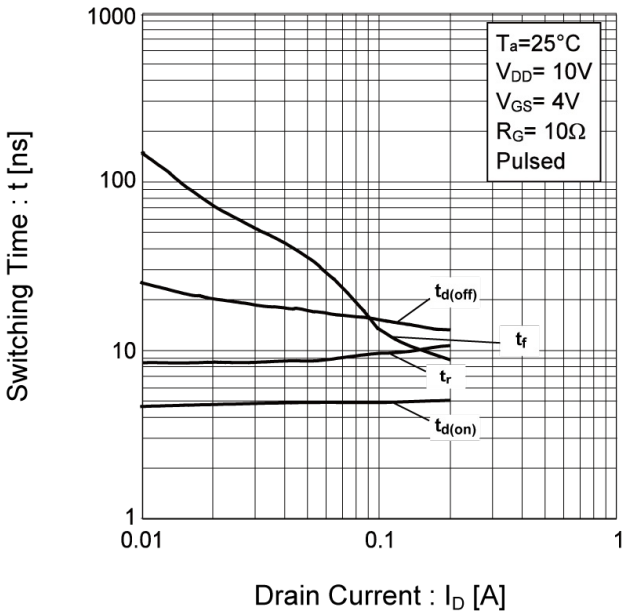
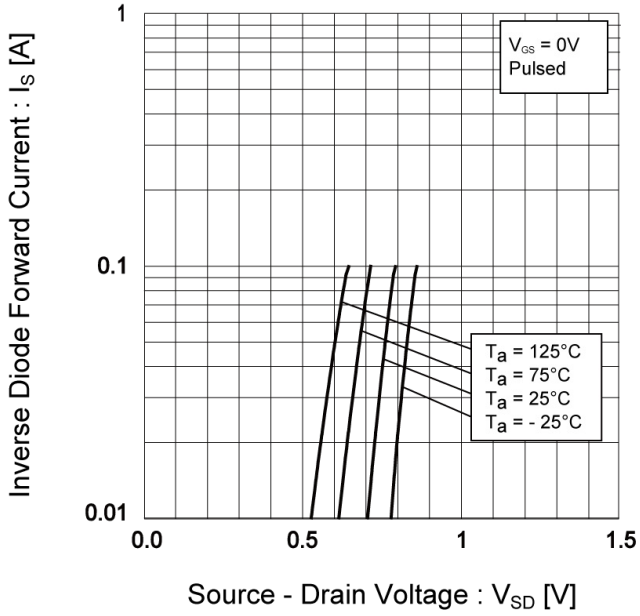


Fig.18 Source Current vs. Source Drain Voltage



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

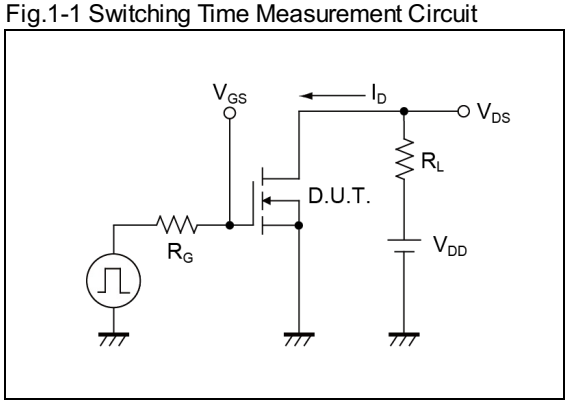
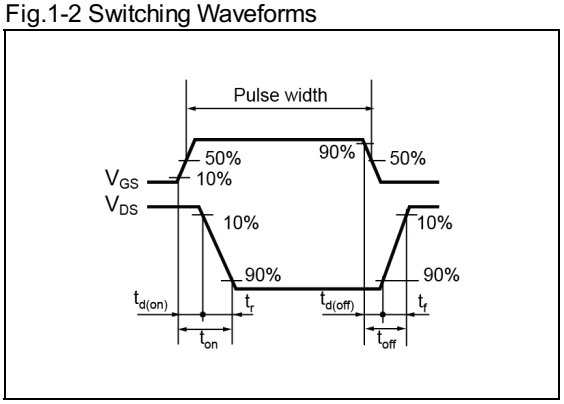
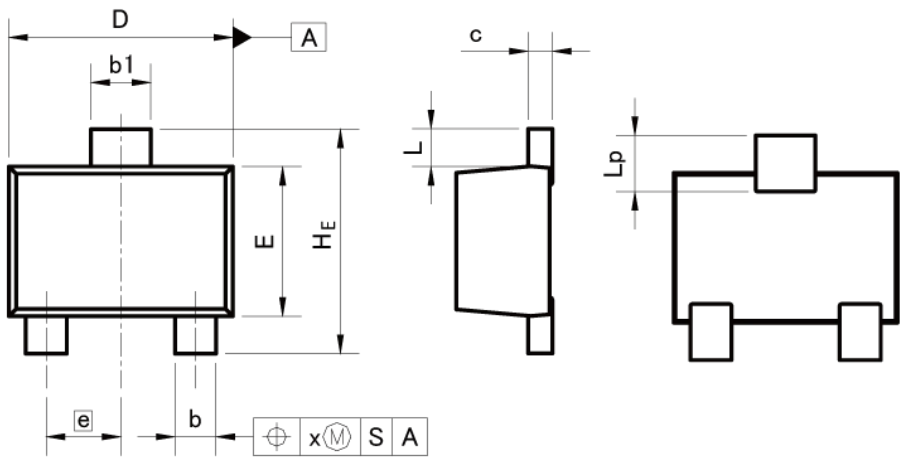


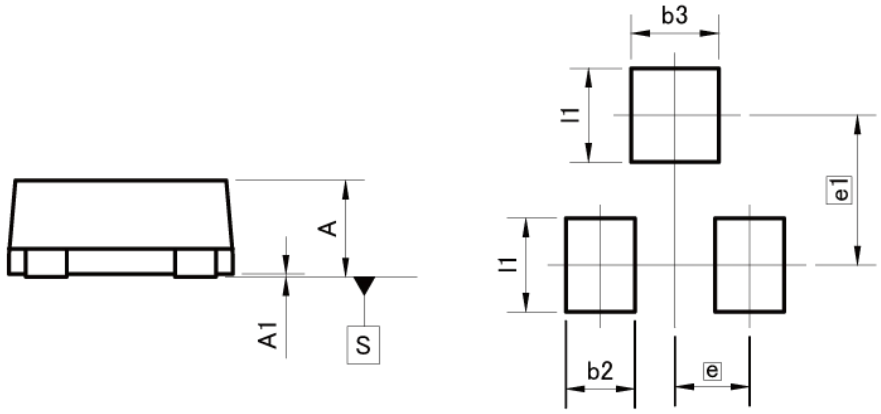
Fig.1-2 Switching Waveforms



●Dimensions

SOT-723
SC-105AA
(VMT3)





Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
c	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
e	0.40		0.02	
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	0.012
Lp	0.20	0.40	0.008	0.016
x	–	0.10	–	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	–	0.37	–	0.015
b3	–	0.47	–	0.019
e1	0.80		0.031	
l1	–	0.50	–	0.020

Dimension in mm/inches

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